



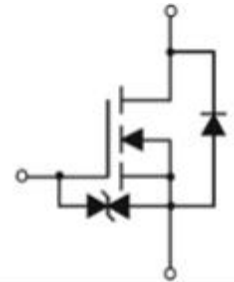
N-Power MOSFET Wafer Datasheet

FEATURES

- Die in 8" Wafer Form
- 60V, 340mA*, N-channel
- Sampling Tested at Probe
- ESD 2KV

APPLIACTION

- Motor Control
- Power Management Functions



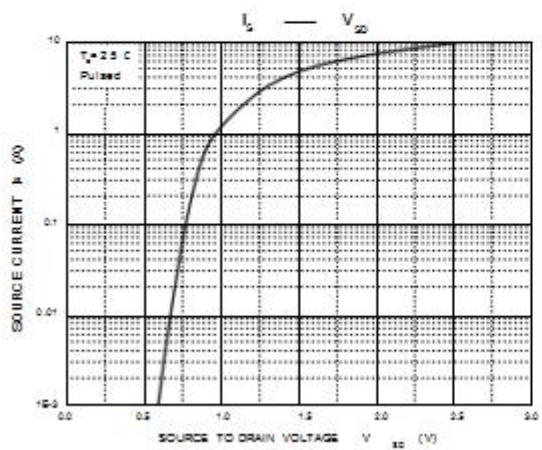
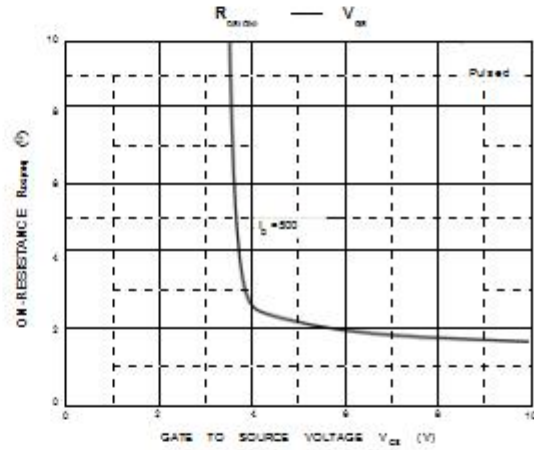
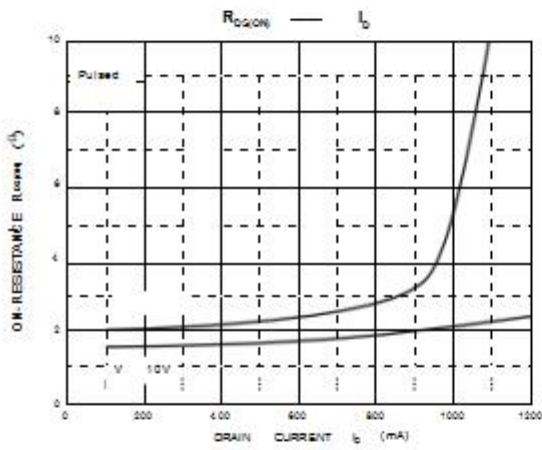
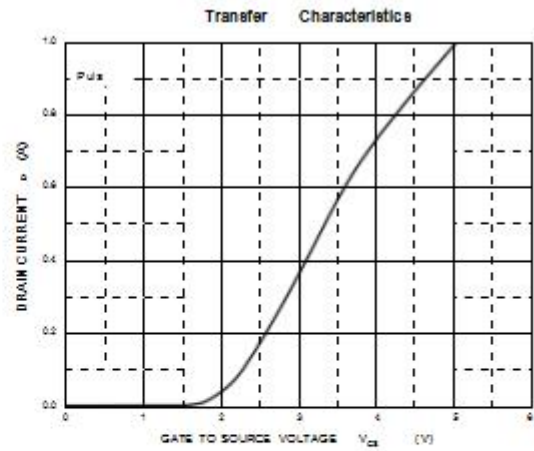
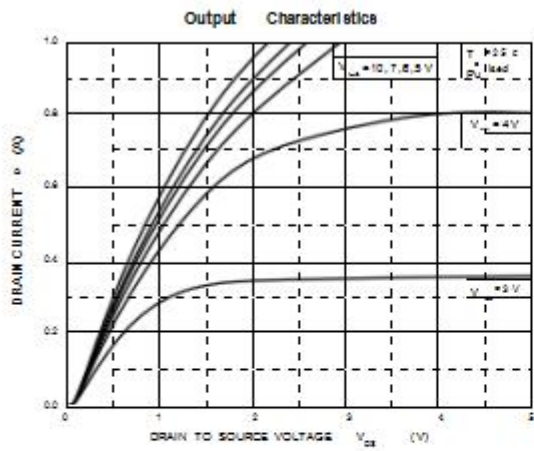
Electrical Characteristics (T_J=25°C)

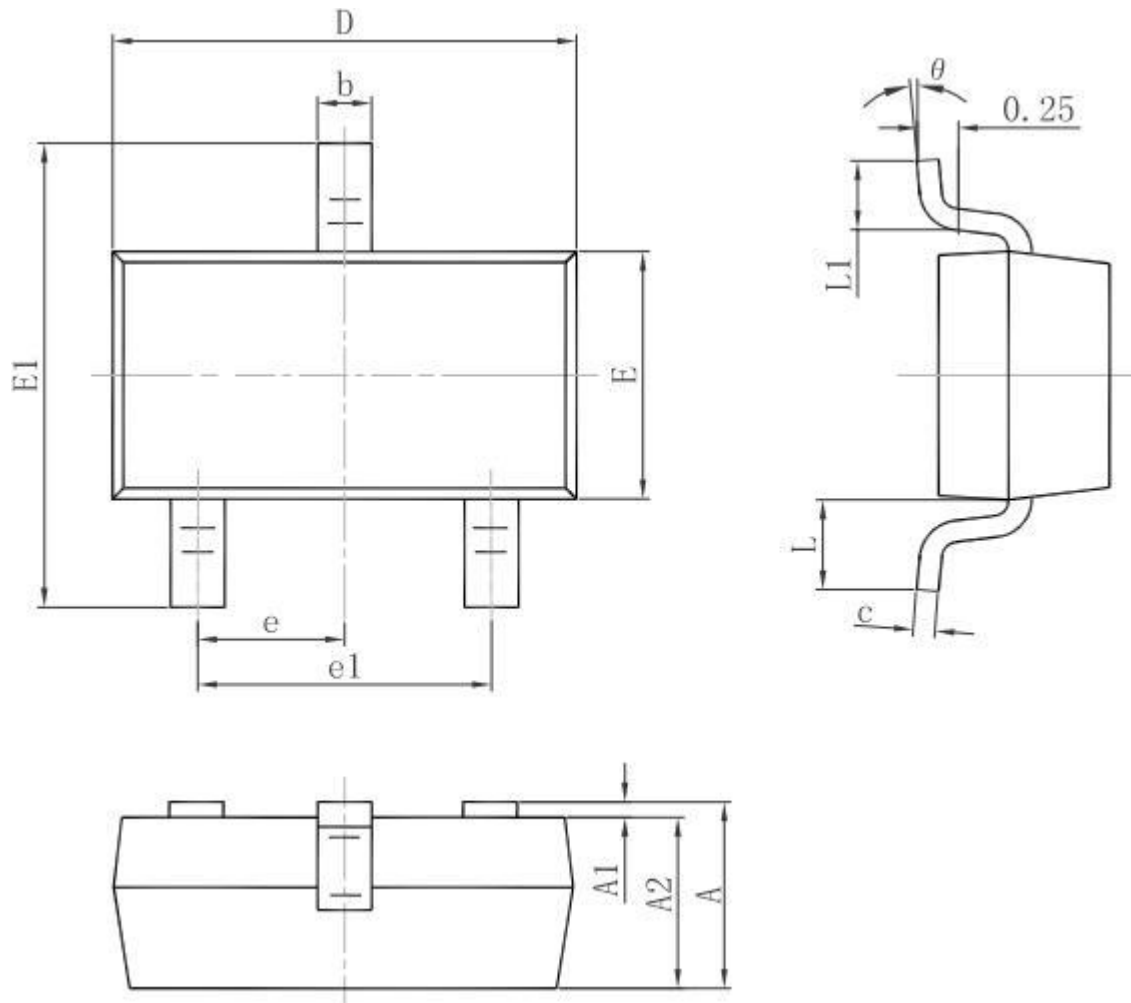
Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{(BR)DSS}	Drain-Source Breakdown Voltage	62	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(ON)}	Static Drain-Source On-Resistance	—	—	2.85	Ω	V _{GS} = 10V, I _D = 500mA
		—	—	3.8	Ω	V _{GS} = 5V, I _D = 200mA
		—	—	4	Ω	V _{GS} = 4V, I _D = 200mA
V _{GS(th)}	Gate Threshold Voltage	1.3	—	2.45	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
I _{GSS}	Gate-Body Leakage Current	—	—	±7	μA	V _{DS} = 0V, V _{GS} = ±20V
		—	—	±350	nA	V _{DS} = 0V, V _{GS} = ±10V
T _J , T _{STG}	Operating and Storage Temperature Range	-55°C to 150°C Max				

Note: Base on package type:



RATING AND CHARACTERISTIC CURVES (2N7002K)





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°